



# NPN EPITAXIAL SILICON TRANSISTORS

# WMBTA92

<b>High Voltage Transistor</b>		<b>SOT—23</b>				
<ul style="list-style-type: none"> <li>* Die Size 0.6X0.6mm</li> <li>* Power Dissipation: 225mW</li> <li>* Collector Current : Max 500mA</li> <li>* Bonding Pad Size                Emittoe 100*100mkm                base 100*100mkm</li> </ul>				1. BASE 2. EMITTER 3. COLLECTOR		
<b>GUARANTEED PROBED CHARACTERISTICS (T<sub>A</sub>=25°C)</b>						
Characteristic	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> =1.0mA	300	-	-	V
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> =100uA	300	-	-	V
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> =10uA	5.0	-	-	V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =260V	-	-	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =6V	-	-	100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	30	-	-	
		V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	40			
		V <sub>CE</sub> =10V, I <sub>C</sub> =30mA	40			
Base-Emitter Saturation Voltage	V <sub>BEsat</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA	-	-	0.90	V
Collector-Emitter Saturation Voltage	V <sub>CEsat</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA	-	-	0.35	V
Transition Frequency	f <sub>r</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=10MHz	50	-	-	MHz
Collector-Base Capacitance	C <sub>cb</sub>	V <sub>CB</sub> =20V, f=1MHz	-	-	6.0	pF
<b>NOTES:</b> Due to probe testing limitations, only the DC parameters are tested.						